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B
E. Willis
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PATENT
Case No. 10519/30

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

Vivek Subramanian et al.

Serial No.: Not yet assigned

Filed: Herewith

For: VERTICALLY STACKED FIELD
PROGRAMMABLE NONVOLATILE
MEMORY AND METHOD OF
FABRICATION

Group Art Unit:

Examiner:

Commissioner for Patents
Washington, D.C. 20231

PRELIMINARY AMENDMENT

Dear Sir:

Prior to commencing the examination of the above-referenced application, please enter the following amendment.

IN THE CLAIMS:

Please cancel claims 1-94.

Please [✓]add the following new claims:

95.
1. (New) A process for fabricating a state change element in a 3-D semiconductor memory device comprising the steps of:
forming a semiconductor layer; and
oxidizing at least a portion of the semiconductor layer in a plasma to form an oxide antifuse layer overlying the semiconductor layer.

Rule 1.126
Sub
C1